

Hugo Navarro

List of Publications by Year in descending order

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82
papers

1,381
citations

394421

19
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377865

34
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82
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82
docs citations

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times ranked

1684
citing authors

#	ARTICLE	IF	CITATIONS
19	Surface-Enhanced Raman Spectroscopy of Acetyl-neuraminic Acid on Silver Nanoparticles: Role of the Passivating Agent on the Adsorption Efficiency and Amplification of the Raman Signal. <i>Journal of Physical Chemistry C</i> , 2017, 121, 21045-21056.	3.1	8
20	Diagnosis of breast cancer by analysis of sialic acid concentrations in human saliva by surface-enhanced Raman spectroscopy of silver nanoparticles. <i>Nano Research</i> , 2017, 10, 3662-3670.	10.4	65
21	High sensitivity bolometers from thymine functionalized multi-walled carbon nanotubes. <i>Sensors and Actuators B: Chemical</i> , 2017, 238, 880-887.	7.8	11
22	Effect of Graphene Oxide on Bacteria and Peripheral Blood Mononuclear Cells. <i>Journal of Applied Biomaterials and Functional Materials</i> , 2016, 14, 423-430.	1.6	3
23	Analysis of cytotoxic effects of silver nanoclusters on human peripheral blood mononuclear cells $\hat{\text{a}}^{\text{c}} \text{in vitro}$. <i>Journal of Applied Toxicology</i> , 2015, 35, 1189-1199.	2.8	30
24	Bolometric Properties of Semiconducting and Metallic Single-Walled Carbon Nanotube Composite Films. <i>ACS Photonics</i> , 2015, 2, 334-340.	6.6	23
25	Determination of the Thermal Expansion Coefficient of Single-Wall Carbon Nanotubes by Raman Spectroscopy. <i>Spectroscopy Letters</i> , 2015, 48, 139-143.	1.0	8
26	Photoluminescence shift in frustules of two pennate diatoms and nanostructural changes to their pores. <i>Luminescence</i> , 2014, 29, 969-976.	2.9	11
27	Structural and Optical Properties of Ge _{1-x} Sn _x Alloys Grown on GaAs (001) by R. F. Magnetron Sputtering. <i>ECS Transactions</i> , 2014, 64, 393-400.	0.5	0
28	High-speed high-sensitivity carbon nanotube-based composite bolometers. <i>Proceedings of SPIE</i> , 2013, , .	0.8	1
29	Ge _{1-x} Sn _x Alloys Pseudomorphically Grown on Ge (001) by Sputtering. <i>ECS Transactions</i> , 2013, 50, 413-417.	0.5	0
30	Functionalization of nitrogen-doped carbon nanotubes with gallium to form Ga-CN _x -multi-wall carbon nanotube hybrid materials. <i>Nanotechnology</i> , 2012, 23, 325601.	2.6	9
31	Evolution of biofilms during the colonization process of pyrite by <i>Acidithiobacillus thiooxidans</i> . <i>Applied Microbiology and Biotechnology</i> , 2012, 93, 763-775.	3.6	17
32	High-Sensitivity Bolometers from Self-Oriented Single-Walled Carbon Nanotube Composites. <i>ACS Applied Materials & Interfaces</i> , 2011, 3, 3200-3204.	8.0	46
33	Interfacial insights of pyrite colonized by <i>Acidithiobacillus thiooxidans</i> cells under acidic conditions. <i>Hydrometallurgy</i> , 2010, 103, 35-44.	4.3	19
34	Infrared study of the absorption edge of $\hat{\text{i}}^2$ -InN films grown on GaN/MgO structures. <i>Journal of Applied Physics</i> , 2010, 108, .	2.5	4
35	Critical thickness of $\hat{\text{i}}^2$ -InN/GaN/MgO structures. <i>Journal of Applied Physics</i> , 2010, 107, 083510.	2.5	11
36	Infrared reflectance anisotropy of wurzite GaN. <i>Journal of Applied Physics</i> , 2009, 106, 063523.	2.5	0

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37	In situ measurements of the critical thickness for strain relaxation in $\text{In}^2\text{-GaN/MgO}$ structures. <i>Journal of Crystal Growth</i> , 2009, 311, 1302-1305.	1.5	8
38	Low energy shifted photoluminescence of Er^{3+} incorporated in amorphous hydrogenated silicon-germanium alloys. <i>Journal of Non-Crystalline Solids</i> , 2009, 355, 976-981.	3.1	1
39	Controlling the dimensions, reactivity and crystallinity of multiwalled carbon nanotubes using low ethanol concentrations. <i>Chemical Physics Letters</i> , 2008, 453, 55-61.	2.6	66
40	Nonlinear behavior of the energy gap in $\text{Ge}_{1-x}\text{Sn}_x$ alloys at 4K. <i>Applied Physics Letters</i> , 2007, 91, .	3.3	43
41	AFM and FTIR characterization of microcrystalline Si obtained from isothermal annealing of Al/a-Si:H. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007, 204, 1014-1017.	1.8	1
42	Lattice vibrations study of $\text{Ga}_{1-x}\text{In}_x\text{As}_y\text{Sb}_{1-y}$ quaternary alloys with low (In, As) content grown by liquid phase epitaxy. <i>Journal of Physics: Conference Series</i> , 2006, 28, 147-150.	0.4	3
43	In-plane and out-of-plane lattice parameters of [11n] epitaxial strained layers. <i>Journal of Crystal Growth</i> , 2006, 291, 340-347.	1.5	10
44	On the bowing parameter in $\text{Cd}_{1-x}\text{Zn}_x\text{Te}$. <i>Journal of Applied Physics</i> , 2004, 95, 6284-6288.	2.5	30
45	Determination of the optical energy gap of $\text{Ge}_{1-x}\text{Sn}_x$ alloys with $0 < x < 0.14$. <i>Applied Physics Letters</i> , 2004, 84, 4532-4534.	3.3	83
46	Raman studies of aluminum induced microcrystallization of n+ Si:H films produced by PECVD. <i>Thin Solid Films</i> , 2003, 445, 32-37.	1.8	5
47	Characterization of GaAs grown by the close-spaced vapor transport technique, using atomic hydrogen as the reactant. <i>Physica Status Solidi A</i> , 2003, 198, 289-296.	1.7	1
48	$\text{Ge}_{1-x}\text{Sn}_x$ alloys pseudomorphically grown on Ge(001). <i>Applied Physics Letters</i> , 2003, 83, 4942-4944.	3.3	45
49	Structural characterization of semi-strained layer $(\text{GaAs})_{1-x}(\text{Si}_2)_x/\text{GaAs}$ multilayers grown by magnetron sputtering. <i>Thin Solid Films</i> , 2002, 416, 49-53.	1.8	0
50	Properties of Portland Cement Pastes Incorporating Nanometer-Sized Franklinite Particles Obtained from Electric Arc Furnace Dust. <i>Journal of the American Ceramic Society</i> , 2001, 84, 2909-2913.	3.8	27
51	STUDY OF STOICHIOMETRIC AND NON-STOICHIOMETRIC CADMIUM SELENIDE THIN FILMS. <i>Modern Physics Letters B</i> , 2001, 15, 741-744.	1.9	7
52	Raman study of luminescent spark processed porous GaAs. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001, 19, 622.	1.6	8
53	Growth of strained-layer GaAs/Ge superlattices by magnetron sputtering: Optical and structural characterization. <i>Journal of Applied Physics</i> , 2001, 89, 3209-3214.	2.5	4
54	Raman scattering study of $(\text{GaAs})_{1-x}(\text{Si}_2)_x$ alloys epitaxially grown on GaAs. <i>Journal of Applied Physics</i> , 2001, 90, 4977-4980.	2.5	6

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55	High purity GaSb grown by LPE in a sapphire boat. Journal of Crystal Growth, 2000, 208, 27-32.	1.5	13
56	Long-range order-disorder transition in (GaAs) _{1-x} (Ge ₂) grown on GaAs(001) and GaAs(111). Microelectronics Journal, 2000, 31, 439-441.	2.0	5
57	Raman scattering study of photoluminescent spark-processed porous InP. Thin Solid Films, 2000, 379, 1-6.	1.8	44
58	Strain in GaAs at the heterointerface of ZnSe/GaAs/GaAs. Journal Physics D: Applied Physics, 1999, 32, 1293-1301.	2.8	1
59	Epitaxial Growth of Strained Ge Films on GaAs(001). Thin Solid Films, 1999, 352, 269-272.	1.8	15
60	Stress in GaAs at the hetero-interface of ZnSe/GaAs/GaAs: a possible effect of pit filling and difference in thermal expansion coefficients. Applied Surface Science, 1999, 151, 271-279.	6.1	6
61	Near band-edge optical properties of GaAs at interfaces of ZnSe/GaAs/GaAs by phase selection in photorefectance. Journal of Applied Physics, 1999, 86, 425-429.	2.5	5
62	Excitonic transitions in (GaAs) _{1-x} (Ge ₂) _x /GaAs multilayers grown by magnetron sputtering. Applied Physics Letters, 1998, 72, 94-96.	3.3	4
63	Microstructure of spark-processed blue luminescent CdTe, GaSb, and InSb. Thin Solid Films, 1996, 281-282, 552-555.	1.8	7
64	Refractive indices of zincblende structure $\hat{I}^2\hat{a}\hat{e}\hat{G}\hat{a}\hat{N}(001)$ in the subband-gap region (0.7-3.3 eV). Applied Physics Letters, 1996, 68, 441-443.	3.3	22
65	Temperature-dependent optical band gap of the metastable zinc-blende structure $\hat{I}^2\text{-Ga}\hat{N}$. Physical Review B, 1994, 50, 8433-8438.	3.2	200
66	Photoconductivity of erbium-doped germanium. Applied Physics A: Solids and Surfaces, 1994, 59, 373-379.	1.4	1
67	Observation of confinement effects on acceptors in Si/Si _{1-x} Gex superlattices. Solid State Communications, 1994, 90, 311-316.	1.9	3
68	Saturation of ionization edge absorption by donors in germanium. Applied Physics A: Solids and Surfaces, 1993, 56, 22-28.	1.4	5
69	Application of photothermal ionization spectroscopy to the study of epitaxially grown germanium on silicon. Journal of Applied Physics, 1992, 72, 3550-3553.	2.5	2
70	Photothermal ionisation spectroscopy of oxygen-related shallow defects in crystalline silicon. Applied Physics A: Solids and Surfaces, 1989, 48, 41-47.	1.4	34
71	High sensitivity detection of trace impurities in the presence of other impurity species: The shallow thermal donors in Cz-Silicon. Mikrochimica Acta, 1988, 94, 415-418.	5.0	0
72	Study of the fundamental linewidths of $1S\hat{t}^1n\hat{P}$ donor transitions in ultrapure germanium. Physical Review B, 1988, 37, 10822-10828.	3.2	23

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73	The Zeeman spectra of phosphorus and the D(H,O) donor complex in ultra-pure germanium. Journal of Physics C: Solid State Physics, 1988, 21, 1511-1520.	1.5	5
74	Experimental study of three ground state components of the hydrogen-oxygen donor in germanium. Solid State Communications, 1987, 64, 1297-1303.	1.9	9
75	New oxygen related shallow thermal donor centres in Czochralski-grown silicon. Solid State Communications, 1986, 58, 151-155.	1.9	62
76	Electroreflectance, photorefectance, and photoabsorption properties of polycrystalline CdTe thin films prepared by the gradient recrystallization and growth technique. Journal of Applied Physics, 1985, 58, 2066-2069.	2.5	18
77	Raman scattering from phonons and magnons in antiferromagnetic Fe ₃ BO ₆ . Solid State Communications, 1984, 50, 331-333.	1.9	5
78	Study of the photoluminescence spectrum in high purity CdTe. Journal of Luminescence, 1983, 28, 163-176.	3.1	23
79	Far-infrared study of the Zeeman effect of indirect excitons in germanium. Physical Review B, 1982, 25, 1141-1150.	3.2	3
80	Emission properties in electrolytically prepared CdTe p-n junctions. Applied Physics Letters, 1981, 39, 433-434.	3.3	14
81	Far-infrared absorption by excitons in silicon. Solid State Communications, 1978, 25, 217-219.	1.9	23
82	The far-infrared absorption spectrum of electron-hole drops in silicon. Solid State Communications, 1978, 25, 1045-1048.	1.9	12